

# **S-19190 Series**

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# AUTOMOTIVE, 105°C OPERATION, VOLTAGE MONITORING IC WITH CELL BALANCING FUNCTION

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The S-19190 Series is a voltage monitoring IC with a cell balancing function and includes a high-accuracy voltage detection circuit and a delay circuit.

The S-19190 Series is suitable for cell balancing and overcharge protection of batteries and capacitors.

Caution This product can be used in vehicle equipment and in-vehicle equipment. Before using the product in the purpose, contact to ABLIC Inc. is indispensable.

#### ■ Features

· High-accuracy voltage detection circuit

Cell balancing detection voltage: 2.0 V to 4.6 V (5 mV step) Accuracy  $\pm 12$  mV (2.0 V  $\leq$  V<sub>BU</sub> < 2.4 V)

Accuracy  $\pm 0.5\%$  (2.4 V  $\leq$  V<sub>BU</sub>  $\leq$  4.6 V)

Cell balancing release voltage: 2.0 V to 4.6  $V^{*1}$  Accuracy  $\pm 24$  mV (2.0 V  $\leq$  V<sub>BL</sub> < 2.4 V)

Accuracy  $\pm 1.0\%$  (2.4 V  $\leq$  V<sub>BL</sub>  $\leq$  4.6 V)

Overcharge detection voltage: 2.0 V to 4.6 V (5 mV step) Accuracy  $\pm 12$  mV (2.0 V  $\leq$  V<sub>CU</sub> < 2.4 V)

Accuracy  $\pm 0.5\%$  (2.4 V  $\leq$  V<sub>CU</sub>  $\leq$  4.6 V)

Overcharge release voltage: 2.0 V to 4.6  $V^{*2}$  Accuracy  $\pm 24$  mV (2.0 V  $\leq$  V<sub>CL</sub> < 2.4 V)

Accuracy  $\pm 1.0\%$  (2.4 V  $\leq$  V<sub>CL</sub>  $\leq$  4.6 V)

• Built-in Nch transistor with ON resistance of 5  $\Omega$  typ. between the CB pin and the VSS pin

• Current consumption: 2.0  $\mu$ A max. (Ta = +25°C)

Delay times are generated only by an internal circuit (External capacitors are unnecessary).

• CO pin output form and output logic are selectable: CMOS output Active "H", active "L"

Nch open-drain output Active "H", active "L"

• Switchable to power-saving mode by using the  $\overline{\text{CE}}$  pin

• Operation temperature range:  $Ta = -40^{\circ}C \text{ to } +105^{\circ}C$ 

- Lead-free (Sn 100%), halogen-free
- AEC-Q100 qualified\*<sup>5</sup>
- \*1. Cell balancing release voltage = Cell balancing detection voltage Cell balancing hysteresis voltage (Cell balancing hysteresis voltage can be selected as 0 V or from a range of 0.1 V to 0.7 V in 50 mV step.)
- \*2. Overcharge release voltage = Overcharge detection voltage Overcharge hysteresis voltage (Overcharge hysteresis voltage can be selected as 0 V or from a range of 0.1 V to 0.7 V in 50 mV step.)
- \*3. Contact our sales office for details.

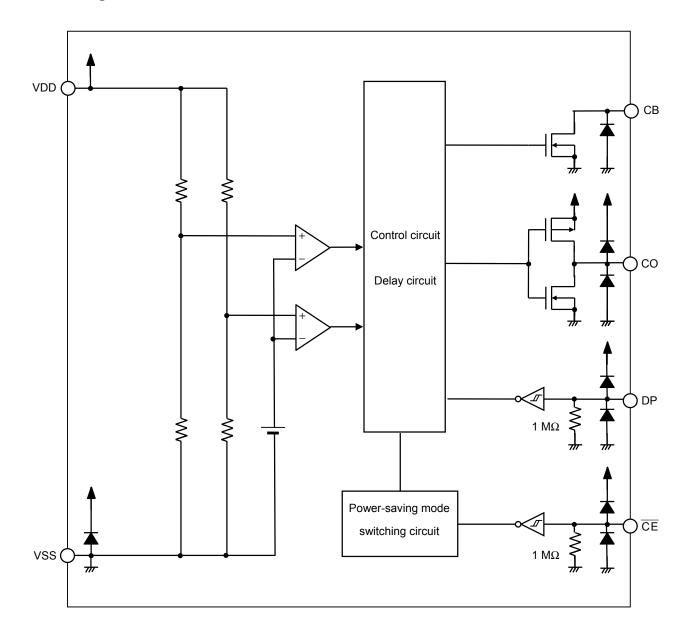
### ■ Applications

- · Rechargeable battery module
- · Capacitor module

#### ■ Package

• SOT-23-6

# ■ Block Diagram



**\*1.** All diodes shown in the figure are parasitic diodes.

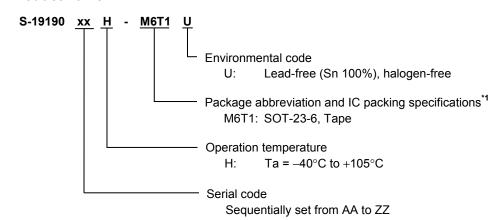
Figure 1

## ■ AEC-Q100 Qualified

This IC supports AEC-Q100 for operation temperature grade 2. Contact our sales office for details of AEC-Q100 reliability specification.

## **■ Product Name Structure**

#### 1. Product name



\*1. Refer to the tape drawing.

#### 2. Package

**Table 1 Package Drawing Codes** 

Package Name	Dimension	Таре	Reel
SOT-23-6	MP006-A-P-SD	MP006-A-C-SD	MP006-A-R-SD

#### 3. Product name list

Table 2 (2 / 1)

	Cell Balancing	Cell Balancing	Overcharge	Overcharge			
Product Name	Detection	Release	Detection	Release	CO Pin	CO Pin	Combination of
Floudet Name	Voltage	Voltage	Voltage	Voltage	Output Form	Output Logic	Delay Time
	[V <sub>BU</sub> ]	$[V_{BL}]$	[V <sub>CU</sub> ]	[V <sub>CL</sub> ]			
S-19190AAH-M6T1U	2.600 V	2.600 V	2.750 V	2.750 V	CMOS output	Active "H"	(1)
S-19190ABH-M6T1U	3.000 V	3.000 V	3.150 V	3.150 V	CMOS output	Active "H"	(1)
S-19190ACH-M6T1U	3.000 V	3.000 V	3.200 V	3.200 V	CMOS output	Active "H"	(1)
S-19190ADH-M6T1U	3.100 V	3.100 V	3.250 V	3.250 V	CMOS output	Active "H"	(1)
S-19190AEH-M6T1U	3.100 V	3.100 V	3.300 V	3.300 V	CMOS output	Active "H"	(1)
S-19190AFH-M6T1U	2.600 V	2.600 V	2.800 V	2.800 V	CMOS output	Active "H"	(1)
S-19190AGH-M6T1U	2.400 V	2.400 V	2.900 V	2.900 V	CMOS output	Active "H"	(1)
S-19190AHH-M6T1U	2.400 V	2.400 V	3.000 V	3.000 V	CMOS output	Active "H"	(1)
S-19190AIH-M6T1U	2.100 V	2.100 V	3.000 V	3.000 V	CMOS output	Active "H"	(1)
S-19190AKH-M6T1U	2.400 V	2.400 V	3.200 V	3.200 V	CMOS output	Active "H"	(1)
S-19190ALH-M6T1U	2.100 V	2.000 V	3.200 V	3.200 V	CMOS output	Active "H"	(1)
S-19190AMH-M6T1U	2.620 V	2.520 V	2.800 V	2.700 V	CMOS output	Active "H"	(1)
S-19190ANH-M6T1U	3.300 V	3.300 V	4.080 V	3.930 V	CMOS output	Active "H"	(1)
S-19190AOH-M6T1U	2.000 V	2.000 V	3.000 V	3.000 V	CMOS output	Active "H"	(1)
S-19190APH-M6T1U	3.700 V	3.700 V	4.500 V	4.500 V	CMOS output	Active "H"	(1)
S-19190AQH-M6T1U	3.800 V	3.800 V	4.080 V	3.930 V	CMOS output	Active "H"	(1)
S-19190ARH-M6T1U	2.800 V	2.800 V	3.150 V	3.150 V	CMOS output	Active "H"	(1)

Table 2 (2 / 2)

				· · ·			
	Cell Balancing	Cell Balancing	Overcharge	Overcharge			
Product Name	Detection	Release	Detection	Release	CO Pin	CO Pin	Combination of
1 Toddot Name	Voltage	Voltage	Voltage	Voltage	Output Form	Output Logic	Delay Time
	[V <sub>BU</sub> ]	[V <sub>BL</sub> ]	[V <sub>CU</sub> ]	[V <sub>CL</sub> ]			
S-19190ASH-M6T1U	2.800 V	2.800 V	3.200 V	3.200 V	CMOS output	Active "H"	(1)
S-19190ATH-M6T1U	2.800 V	2.800 V	3.100 V	3.100 V	CMOS output	Active "H"	(1)
S-19190AUH-M6T1U	2.500 V	2.400 V	3.800 V	3.700 V	CMOS output	Active "H"	(1)
S-19190AVH-M6T1U	2.300 V	2.200 V	3.800 V	3.700 V	CMOS output	Active "H"	(1)
S-19190AWH-M6T1U	2.650 V	2.600 V	2.750 V	2.650 V	Nch open-drain output	Active "L"	(1)
S-19190AXH-M6T1U	2.400 V	2.400 V	2.950 V	2.950 V	CMOS output	Active "H"	(1)
S-19190AYH-M6T1U	4.150 V	4.150 V	4.275 V	4.275 V	CMOS output	Active "H"	(2)
S-19190AZH-M6T1U	2.450 V	2.450 V	2.500 V	2.500 V	CMOS output	Active "H"	(3)
S-19190BDH-M6T1U	2.300 V	2.300 V	2.600 V	2.600 V	CMOS output	Active "H"	(1)
S-19190BEH-M6T1U	4.400 V	4.200 V	4.600 V	4.600 V	CMOS output	Active "H"	(3)
S-19190BFH-M6T1U	3.550 V	3.200 V	4.080 V	3.380 V	CMOS output	Active "L"	(4)
S-19190BGH-M6T1U	2.700 V	2.000 V	4.400 V	3.700 V	CMOS output	Active "H"	(3)
S-19190BHH-M6T1U	3.550 V	3.550 V	3.800 V	3.700 V	CMOS output	Active "L"	(4)
S-19190BIH-M6T1U	2.700 V	2.000 V	4.400 V	4.200 V	CMOS output	Active "H"	(3)
S-19190BJH-M6T1U	2.725 V	2.675 V	2.775 V	2.725 V	CMOS output	Active "L"	(4)

Remark 1. Please contact our sales office for products other than the above.

- 2. Set  $V_{CU} > V_{BU}$ .
- 3. Refer to Table 3 for details about combinations of delay times.

Table 3

Combination of	Cell Balancing	Cell Balancing	Overcharge	0vercharge Release
Combination of	Detection Delay Time	Release Delay Time	Detection Delay Time	Delay Time
Delay Time	[t <sub>BU</sub> ]	[t <sub>BL</sub> ]	[t <sub>CU</sub> ]	[t <sub>CL</sub> ]
(1)	128 ms	1.0 ms	128 ms	1.0 ms
(2)	128 ms	1.0 ms	1024 ms	1.0 ms
(3)	64 ms	0.5 ms	64 ms	0.5 ms
(4)	128 ms	1.0 ms	1024 ms	2.0 ms

Remark The delay times can be changed within the ranges listed above. For details, please contact our sales office.

Table 4

Delay Time	Symbol		Selection Range						Remark
Cell balancing detection delay time*1	t <sub>BU</sub>	64 ms	128 ms*2		256 ms	51	2 ms	1024 ms	Select a value from the left.
Cell balancing release delay time	t <sub>BL</sub>	0.5 ms	S	1.0 ms*2			2.0 ms		Select a value from the left.
Overcharge detection delay time*1	t <sub>CU</sub>	64 ms	128 r	128 ms <sup>*2</sup> 256 m		512 ms		1024 ms	Select a value from the left.
Overcharge release delay time	t <sub>CL</sub>	0.5 ms	1.0 ms*2		1.0 ms <sup>*2</sup> 2.0 ms		.0 ms	Select a value from the left.	

<sup>\*1.</sup> Set  $t_{CU} \ge t_{BU}$ .

<sup>\*2.</sup> The value is the delay time of the standard products.

# **■** Pin Configuration

## 1. SOT-23-6

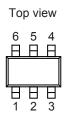


Figure 2

		Table 5
Pin No.	Symbol	Description
1	СО	Output pin for overcharge signal
2	VSS	Input pin for negative power supply
3	DP	Test mode switching pin "H": Test mode (used to shorten the delay time) "L": Normal operation mode
4	CE	Power-saving mode switching pin "H": Power-saving mode "L": Normal operation mode
5	VDD	Input pin for positive power supply
6	СВ	Output pin for cell balancing signal

(Nch open-drain output)

Table 5

## ■ Absolute Maximum Ratings

Table 6

(Ta = +25°C unless otherwise specified)

Item	Symbol	Applied Pin	Absolute Maximum Rating	Unit
Input voltage between VDD pin and VSS pin	V <sub>DS</sub>	VDD	$V_{\text{SS}} - 0.3$ to $V_{\text{SS}} + 6.0$	V
Input pin voltage	V <sub>IN</sub>	CE, DP	$V_{SS} - 0.3$ to $V_{DD} + 0.3 \le V_{SS} + 6.0$	V
Output pin voltage	V <sub>OUT</sub>	CO, CB	$V_{SS} - 0.3$ to $V_{DD} + 0.3 \le V_{SS} + 6.0$	V
Output pin current	I <sub>CB</sub>	СВ	100 (-40°C to +105°C)	mA
Operation ambient temperature	Topr	_	-40 to +105	°C
Storage temperature	T <sub>stg</sub>	_	−55 to +125	°C

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

## **■** Thermal Resistance Value

Table 7

Item	Symbol	Condition		Min.	Тур.	Max.	Unit
	θја	SOT-23-6	Board A	1	159	1	°C/W
			Board B	1	124	ı	°C/W
Junction-to-ambient thermal resistance*1			Board C	1	1	1	°C/W
			Board D	_	-	_	°C/W
			Board E	_	_	_	°C/W

<sup>\*1.</sup> Test environment: compliance with JEDEC STANDARD JESD51-2A

Remark Refer to "■ Power Dissipation" and "Test Board" for details.

## **■** Electrical Characteristics

For details about the test circuits and testing method, refer to "■ Test Circuit".

Caution Unless otherwise specified in Table 8 and Table 9, set V2 = V3 = 0 V, and SWn (n = 1 to 4) = OFF.

1.  $Ta = +25^{\circ}C$ 

Table 8 (1 / 2)

(Ta = +25°C unless otherwise specified)

Item	Symbol		Condition	Min.	Тур.	Max.	Unit
Detection voltage	•					•	
Cell balancing detection	V <sub>BU</sub>	SW1 = ON	$2.0 \text{ V} \le \text{V}_{\text{BU}} < 2.4 \text{ V}$	V <sub>BU</sub> – 0.012	V <sub>BU</sub>	V <sub>BU</sub> + 0.012	V
voltage	<b>V</b> BU	SWI - ON	$2.4~V \leq V_{BU} \leq 4.6~V$	$V_{BU} \times 0.995$	$V_{BU}$	V <sub>BU</sub> × 1.005	V
Cell balancing release	$V_{BL}$	SW1 = ON	$2.0~\textrm{V} \leq \textrm{V}_{\textrm{BL}} < 2.4~\textrm{V}$	$V_{BL}$ – 0.024	$V_{BL}$	V <sub>BL</sub> + 0.024	V
voltage	V BL	3W1 - 0N	$2.4~V \leq V_{BL} \leq 4.6~V$	$V_{BL} \times 0.99$	$V_{BL}$	V <sub>BL</sub> × 1.01	V
Overcharge detection	Vou	2.0 V ≤ V <sub>CU</sub>	< 2.4 V	V <sub>CU</sub> - 0.012	V <sub>CU</sub>	V <sub>CU</sub> + 0.012	V
voltage	$V_{CU}$ 2.4 $V \le V_{CU}$		≤ 4.6 V	$V_{\text{CU}} \times 0.995$	V <sub>CU</sub>	V <sub>CU</sub> × 1.005	V
Overcharge release	V <sub>CL</sub>	$2.0 \text{ V} \le V_{CL} < 2.4 \text{ V}$		V <sub>CL</sub> - 0.024	$V_{CL}$	V <sub>CL</sub> + 0.024	V
voltage	V CL	$2.4~V \leq V_{CL} \leq 4.6~V$		$V_{CL} \times 0.99$	$V_{CL}$	V <sub>CL</sub> × 1.01	٧
Input voltage							
Operation voltage between VDD pin and VSS pin	V <sub>DS</sub>	Voltages ou CB pin are	Itput from CO pin and fixed	1.5	ı	5.0	٧
CE pin voltage "H"	$V_{\overline{CEH}}$		-	ı	I	$V_{DD} \times 0.9$	>
CE pin voltage "L"	$V_{\overline{CEL}}$		-	$V_{DD} \times 0.1$	I	-	>
DP pin voltage "H"	V <sub>DPH</sub>		_	ı	I	$V_{DD} \times 0.9$	>
DP pin voltage "L"	V <sub>DPL</sub>		-	$V_{DD} \times 0.1$	-	-	>
Input current							
Current consumption during operation	I <sub>OPE</sub>	I <sub>VDD</sub> when V	$/1 = V_{BL} - 0.1 V$	ı	1.2	2.0	μΑ
Current consumption during power-saving	I <sub>PSV</sub>	I <sub>VDD</sub> when V	$V_1 = V_2 = V_{BL} - 0.1 V$	-	_	0.1	μΑ

Table 8 (2 / 2)

 $(Ta = +25^{\circ}C \text{ unless otherwise specified})$ 

<del></del>			+25°C ur		1	_
Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Delay time	<del></del>		1		1	1
Cell balancing detection delay time	t <sub>BU</sub>	_	$t_{\text{BU}}\times 0.8$	t <sub>BU</sub>	$t_{\text{BU}} \times 1.2$	ms
Cell balancing release delay time	t <sub>BL</sub>	-	$t_{\text{BL}} \times 0.8$	t <sub>BL</sub>	$t_{\text{BL}} \times 1.2$	ms
Overcharge detection delay time	tcu	-	$t_{\text{CU}}\times 0.8$	tcu	$t_{\text{CU}} \times 1.2$	ms
Overcharge release delay time	t <sub>CL</sub>	-	$t_{\text{CL}} \times 0.8$	t <sub>CL</sub>	$t_{\text{CL}} \times 1.2$	ms
Output current	•					
CB pin output current						
CB pin sink current	I <sub>CBS</sub>	V1 = V <sub>BU</sub> + 0.1 V, SW2 = ON, V4 = 0.5 V	30	_	_	mA
CB pin leakage current	I <sub>CBL</sub>	V1 = V <sub>BL</sub> - 0.1 V, SW2 = ON, V4 = 6.0 V	_	_	0.1	μΑ
CO pin output current (ou	put form:	CMOS output, output logic: activ	ve "H")			
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	_	_	mA
CO pin source current	Ісон	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = V1 - 0.5 V	1.0	-	-	mA
CO pin output current (ou	put form:	CMOS output, output logic: activ	ve "L")			
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	-	_	mA
CO pin source current	Ісон	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = V1 - 0.5 V	1.0	_	_	mA
CO pin output current (ou	tput form:	Nch open-drain output, output le	ogic: activ	/e "H")	1	
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	_	_	mA
CO pin leakage current	I <sub>COHL</sub>	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = 6.0 V	_	_	0.1	μΑ
CO pin output current (ou	but form:	Nch open-drain output, output le	ogic: activ	/e "L")	1	
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	_	_	mA
CO pin leakage current	I <sub>COHL</sub>	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = 6.0 V	_	_	0.1	μΑ

## 2. $Ta = -40^{\circ}C \text{ to } +105^{\circ}C$

Table 9 (1 / 2)

 $(Ta = -40^{\circ}C \text{ to } +105^{\circ}C \text{ unless otherwise specified})$ 

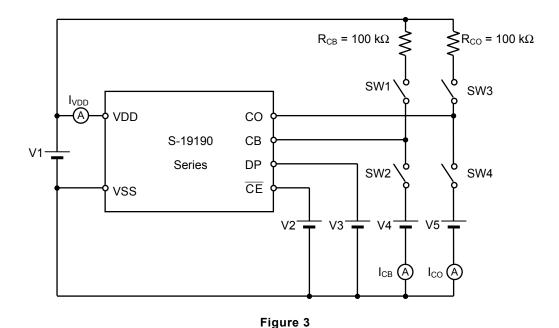
Item	Symbol		Condition	Min.	Тур.	Max.	Unit
Detection voltage		•			71		
Cell balancing detection	V <sub>BU</sub>	SW1 = ON	$2.0 \text{ V} \le \text{V}_{\text{BU}} < 2.4 \text{ V}$	V <sub>BU</sub> - 0.040	$V_{BU}$	V <sub>BU</sub> + 0.040	V
voltage	V BU	3W1 - ON	$2.4~V \leq V_{BU} \leq 4.6~V$	$V_{BU} \times 0.984$	$V_{BU}$	V <sub>BU</sub> × 1.016	V
Cell balancing release	$V_{BL}$	SW1 = ON	$2.0~\textrm{V} \leq \textrm{V}_{\textrm{BL}} < 2.4~\textrm{V}$	$V_{BL}$ $-$ 0.080	$V_{BL}$	V <sub>BL</sub> + 0.080	V
voltage	V BL	3W1 - ON	$2.4~V \leq V_{BL} \leq 4.6~V$	$V_{BL} \times 0.968$	$V_{BL}$	V <sub>BL</sub> × 1.032	V
Overcharge detection	V <sub>CU</sub>	2.0 V ≤ V <sub>CU</sub>	< 2.4 V	V <sub>CU</sub> - 0.040	V <sub>CU</sub>	V <sub>CU</sub> + 0.040	V
voltage	V CU	2.4 V ≤ V <sub>CU</sub>	≤ 4.6 V	$V_{CU} \times 0.984$	$V_{CU}$	V <sub>CU</sub> × 1.016	V
Overcharge release	V <sub>CL</sub>	$2.0 \text{ V} \le \text{V}_{CL} < 2.4 \text{ V}$		V <sub>CL</sub> - 0.080	$V_{CL}$	V <sub>CL</sub> + 0.080	V
voltage	V CL	2.4 V ≤ V <sub>CL</sub>	≤ 4.6 V	$V_{CL} \times 0.968$	$V_{\text{CL}}$	V <sub>CL</sub> × 1.032	V
Input voltage							
Operation voltage between VDD pin and VSS pin	V <sub>DS</sub>	Voltages ou CB pin are	itput from CO pin and fixed	1.5	ı	5.0	٧
CE pin voltage "H"	$V_{\overline{CEH}}$		_	1	ı	$V_{DD} \times 0.9$	V
CE pin voltage "L"	$V_{\overline{CEL}}$		_	$V_{DD} \times 0.1$	-	_	V
DP pin voltage "H"	$V_{DPH}$		_	-	-	$V_{DD} \times 0.9$	V
DP pin voltage "L"	$V_{DPL}$		-	$V_{DD} \times 0.1$	ı	-	٧
Input current							
Current consumption during operation	I <sub>OPE</sub>	I <sub>VDD</sub> when V	$/1 = V_{BL} - 0.1 V$	-	1.2	2.1	μΑ
Current consumption during power-saving	I <sub>PSV</sub>	$I_{VDD}$ when $V$	$/1 = V2 = V_{BL} - 0.1 V$	_	-	0.15	μΑ

Table 9 (2 / 2)

(Ta = -40°C to +105°C unless otherwise specified)

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Delay time	Syllibol	Condition	IVIIII.	ιyp.	IVIAX.	Offic
			1			
Cell balancing detection delay time	t <sub>BU</sub>	-	$t_{\text{BU}}\times 0.5$	t <sub>BU</sub>	$t_{\text{BU}} \times 1.5$	ms
Cell balancing release delay time	t <sub>BL</sub>	-	$t_{\text{BL}} \times 0.5$	$t_{BL}$	$t_{BL} \times 1.5$	ms
Overcharge detection delay time	t <sub>CU</sub>	_	$t_{\text{CU}} \times 0.5$	t <sub>CU</sub>	$t_{\text{CU}} \times 1.5$	ms
Overcharge release delay time	t <sub>CL</sub>	_	$t_{\text{CL}} \times 0.5$	t <sub>CL</sub>	$t_{\text{CL}} \times 1.5$	ms
Output current						
CB pin output current						_
CB pin sink current	I <sub>CBS</sub>	$V1 = V_{BU} + 0.1 \text{ V}, \text{ SW2} = \text{ON},$ V4 = 0.5  V	30	_	_	mA
CB pin leakage current	I <sub>CBL</sub>	V1 = V <sub>BL</sub> - 0.1 V, SW2 = ON, V4 = 6.0 V	_	_	0.15	μΑ
CO pin output current (out	put form:	CMOS output, output logic: acti	ve "H")			
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	_	_	mA
CO pin source current	Ісон	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = V1 - 0.5 V	1.0	-	-	mA
CO pin output current (out	put form:	CMOS output, output logic: acti	ve "L")			
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	-	-	mA
CO pin source current	Ісон	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = V1 - 0.5 V	1.0	_	_	mA
CO pin output current (out	put form:	Nch open-drain output, output le	ogic: activ	/e "H")	II.	
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	-	_	mA
CO pin leakage current	I <sub>COHL</sub>	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = 6.0 V	-	-	0.15	μΑ
CO pin output current (out	put form:	Nch open-drain output, output le	ogic: activ	/e "L")	L	
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	-	_	mA
CO pin leakage current	I <sub>COHL</sub>	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = 6.0 V	_	-	0.15	μΑ

#### **■** Test Circuit



Caution Unless otherwise specified in Table 8, set V2 = V3 = 0 V, and SWn (n = 1 to 4) = OFF.

1. CE pin voltage "H"

 $\overline{\text{CE}}$  pin voltage "H" ( $V_{\overline{\text{CEH}}}$ ) is defined as the voltage at which  $I_{VDD}$  is changed from  $I_{OPE}$  to  $I_{PSV}$  when V2 is increased from 0 V after setting V1 =  $V_{BL}$  – 0.1 V.

## 2. CE pin voltage "L"

 $\overline{\text{CE}}$  pin voltage "L" ( $V_{\overline{\text{CEL}}}$ ) is defined as the voltage at which  $I_{VDD}$  is changed from  $I_{PSV}$  to  $I_{OPE}$  when V2 is decreased from  $V_{BL} - 0.1$  V after setting V1 = V2 =  $V_{BL} - 0.1$  V.

## 3. DP pin voltage "H"\*1

DP pin voltage "H" ( $V_{DPH}$ ) is defined as the voltage at which the test mode is switched when V3 is increased from 0 V after setting V1 =  $V_{BL}$  – 0.1 V.

## 4. DP pin voltage "L" \*1

DP pin voltage "L" ( $V_{DPL}$ ) is defined as the voltage at which the normal operation mode is switched when V3 is decreased from  $V_{BL} - 0.1$  V after setting V1 = V3 =  $V_{BL} - 0.1$  V.

#### 5. Cell balancing detection delay time

Cell balancing detection delay time ( $t_{BU}$ ) is defined as the time from when SW1 is set to ON and V1 is set to  $V_{BU}$  – 0.1 V to when the CB pin output is inverted after setting V1 to  $V_{BU}$  + 0.1 V.

#### 6. Cell balancing release delay time

Cell balancing release delay time ( $t_{BL}$ ) is defined as the time from when SW1 is set to ON and V1 is set to  $V_{BL}$  + 0.1 V to when the CB pin output is inverted after setting V1 to  $V_{BL}$  – 0.1 V.

#### 7. Overcharge detection delay time

Overcharge detection delay time ( $t_{CU}$ ) is defined as the time from when SW1 is set to ON and V1 is set to  $V_{CU}$  – 0.1 V to when the CO pin output is inverted after setting V1 to  $V_{CU}$  + 0.1 V.

#### 8. Overcharge release delay time

Overcharge release delay time ( $t_{CL}$ ) is defined as the time from when SW1 is set to ON and V1 is set to  $V_{CL}$  + 0.1 V to when the CO pin output is inverted after setting V1 to  $V_{CL}$  – 0.1 V.

\*1. For details about switching to the test mode by using the DP pin, refer to "5. DP pin" in "■ Operation".

#### ■ Standard Circuit

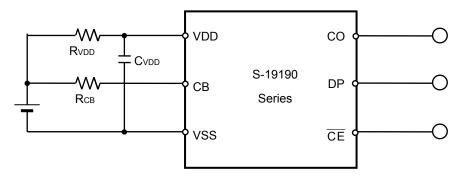


Figure 4

**Table 10 Constants for External Components** 

Symbol	Part	Purpose	Min.	Тур.	Max.	Remark
R <sub>VDD</sub>	Resistor	ESD protection, for power fluctuation control	150 Ω	330 Ω	1.0 kΩ	Resistance should be as small as possible to avoid worsening the overcharge detection accuracy due to current consumption.*1
$C_{VDD}$	Capacitor	For power fluctuation control	0.068 μF	0.1 μF	1.0 μF	Connect a capacitor of 0.068 μF or more between VDD pin and VSS pin.*1
R <sub>CB</sub>	Resistor	For setting the cell balancing current value	ı	_	_	Set the required cell balancing current value depending on "2. Cell balancing status" in "  Operation".*2

<sup>\*1.</sup> When connecting a resistor less than 150  $\Omega$  to R<sub>VDD</sub> or a capacitor less than 0.068  $\mu$ F to C<sub>VDD</sub>, the S-19190 Series may malfunction when power is largely fluctuated.

## Caution 1. The above constants may be changed without notice.

2. The example of connection shown above and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

<sup>\*2.</sup> Set the cell balancing current value so that R<sub>CB</sub> does not exceed the power dissipation.

## ■ Operation

Remark Refer to "■ Standard Circuit ".

#### 1. Normal status

In the S-19190 Series, if the voltage between the VDD pin and the VSS pin  $(V_{DS})$  has not reached the cell balancing detection voltage  $(V_{BU})$ , the CB pin output is in the high-impedance status. The CO pin output status varies according to the output form and output logic selected, as shown in **Table 11**. This is the normal status.

Table 11

CO Pin Output Form and Output Logic	CB Pin Output	CO Pin Output
CMOS output, active "H"	"H"	"L"
CMOS output, active "L"	"H"	"H"
Nch open-drain output, active "H"	"H"	"L"
Nch open-drain output, active "L"	"H"	"H"

#### 2. Cell balancing status

In the S-19190 Series, if  $V_{DS}$  is  $V_{BU}$  or higher and this status continues for the cell balancing detection delay time ( $t_{BU}$ ) or longer, the CB pin output becomes "L". This is the cell balancing status.

The cell balancing status is released when  $V_{DS}$  drops to the cell balancing release voltage ( $V_{BL}$ ) or lower and this status continues for the cell balancing release delay time ( $t_{BL}$ ) or longer.

The S-19190 Series includes an Nch transistor with ON resistance of 5  $\Omega$  typ. (R<sub>CBON</sub>) between the CB pin and the VSS pin, thus causing the cell balancing current (I<sub>CB</sub>) to flow in cell balancing status, and the cell balancing operation to start.

By connecting a resistor ( $R_{CB}$ ) to the CB pin,  $I_{CB}$  in cell balancing status can be calculated by using the following equation.

$$I_{CB} = V_{BU} / (R_{CBON} + R_{CB})$$

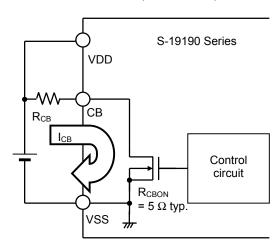


Figure 5

#### 3. Overcharge status

In the S-19190 Series, if  $V_{DS}$  is the overcharge detection voltage ( $V_{CU}$ ) or higher and this status continues for the overcharge detection delay time ( $t_{CU}$ ) or longer, the CO pin output is inverted. The CO pin output status varies according to the output form and output logic selected, as shown in **Table 12**. This is the overcharge status. In the overcharge status, the CB pin output becomes "L".

Table 12

CO Pin Output Form and Output Logic	CB Pin Output	CO Pin Output
CMOS output, active "H"	"L"	"H"
CMOS output, active "L"	"L"	"L"
Nch open-drain output, active "H"	"L"	"H"
Nch open-drain output, active "L"	"L"	"L"

The overcharge status is released when  $V_{DS}$  drops to the overcharge release voltage ( $V_{CL}$ ) or lower and this status continues for the overcharge release delay time ( $t_{CL}$ ) or longer.

#### 4. CE pin

The S-19190 Series has the  $\overline{\text{CE}}$  pin (Power-saving mode switching pin). The S-19190 Series is set to power-saving mode by inputting a voltage of  $V_{\overline{\text{CEH}}}$  or higher to the  $\overline{\text{CE}}$  pin.

Table 13

14510 10				
CE Pin	Status			
Open (V <sub>CE</sub> = V <sub>SS</sub> )	Normal operation mode			
"H" $(V_{\overline{CE}} \ge V_{\overline{CE}H})$	Power-saving mode			
"L" $(V_{\overline{CE}} \le V_{\overline{CEL}})$	Normal operation mode			

In power-saving mode, the current consumption is decreased to current consumption during power-saving (I<sub>PSV</sub>). The CB pin or the CO pin output in power-saving mode is the same as that in the normal status.

The  $\overline{CE}$  pin is pulled down to  $V_{SS}$  by the internal resistor. When in a mode other than power-saving mode, leave the  $\overline{CE}$  pin open or short it with  $V_{SS}$ .

### 5. DP pin

The S-19190 Series has the DP pin (Test mode switching pin). The S-19190 Series is set to test mode (used to shorten the delay time) by inputting a voltage of  $V_{DPH}$  or higher to the DP pin.

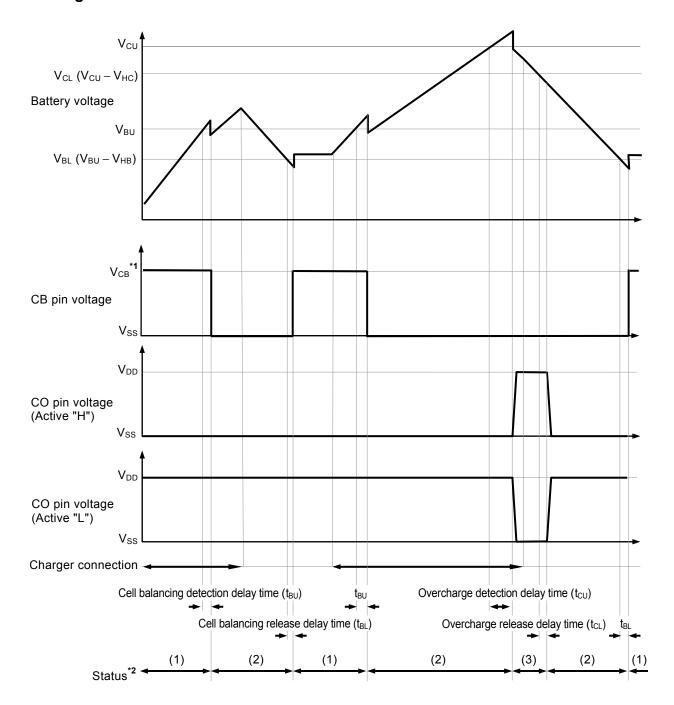
Table 14

DP Pin	Status	
Open (V <sub>DP</sub> = V <sub>SS</sub> )	Normal operation mode	
"H" $(V_{DP} \ge V_{DPH})$	Test mode	
"L" $(V_{DP} \leq V_{DPL})$	Normal operation mode	

In test mode, the cell balancing detection delay time ( $t_{BU}$ ) and overcharge detection delay time ( $t_{CU}$ ) are shortened to 1/64 of the delay time in the normal operation mode.

The DP pin is pulled down to  $V_{SS}$  by the internal resistor. When in a mode other than test mode, leave the DP pin open or short it with  $V_{SS}$ .

# **■** Timing Chart



- \*1. The CB pin is pulled up by the external resistor.
- \*2. (1): Normal status
  - (2): Cell balancing status
  - (3): Overcharge status

Remark The charger is assumed to charge with a constant current.

Figure 6

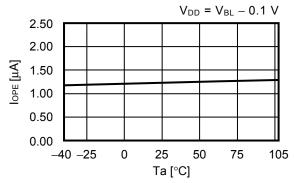
#### ■ Precautions

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- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- ABLIC Inc. claims no responsibility for any and all disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

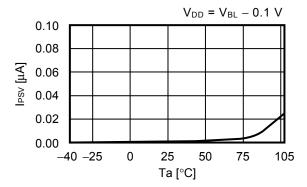
## ■ Characteristics (Typical Data)

## 1. Current consumption

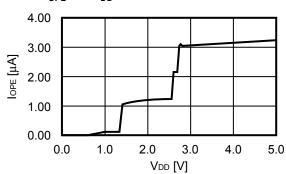
### 1. 1 I<sub>OPE</sub> vs. Ta



1. 2 I<sub>PSV</sub> vs. Ta

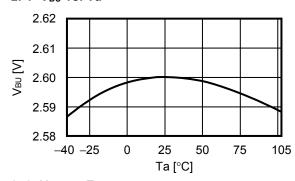


1. 3  $I_{OPE}$  vs.  $V_{DD}$ 

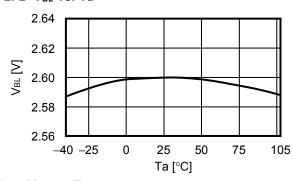


# 2. Cell balancing detection / release voltage, overcharge detection / release voltage and delay times

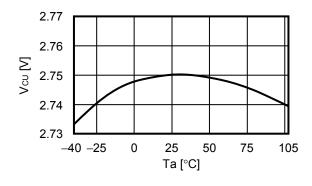
2. 1 V<sub>BU</sub> vs. Ta



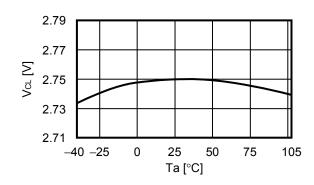
2. 2 V<sub>BL</sub> vs. Ta



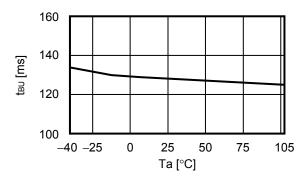
2. 3 V<sub>CU</sub> vs. Ta



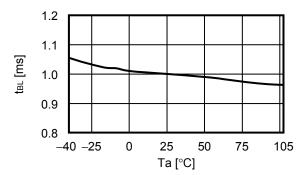
2. 4 V<sub>CL</sub> vs. Ta



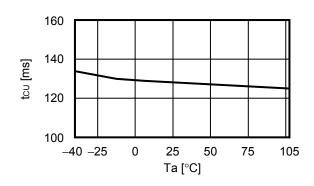
#### 2. 5 t<sub>BU</sub> vs. Ta



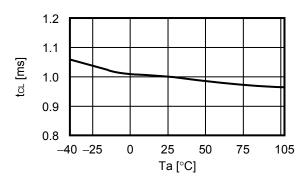
## 2. 6 $t_{\text{BL}}$ vs. Ta



2. 7 tcu vs. Ta

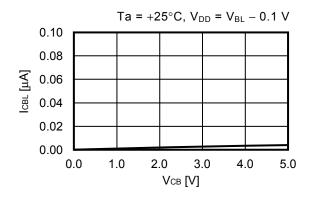


2. 8 t<sub>CL</sub> vs. Ta

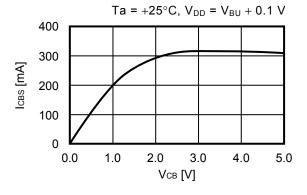


#### 3. Output current

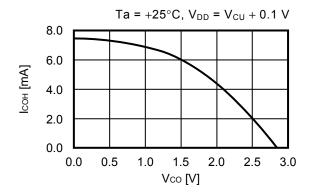
#### 3. 1 ICBL VS. VCB



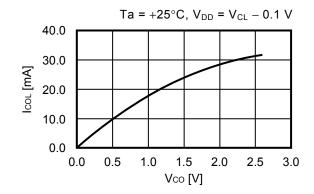
3. 2 ICBS VS. VCB



3. 3 I<sub>COH</sub> vs. V<sub>CO</sub>

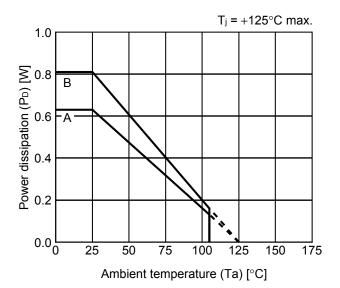


3. 4 Icol vs. Vco



# **■** Power Dissipation

## SOT-23-6



 Board
 Power Dissipation (PD)

 A
 0.63 W

 B
 0.81 W

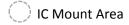
 C

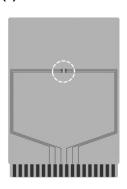
 D

 E

# **SOT-23-3/3S/5/6** Test Board

# (1) Board A





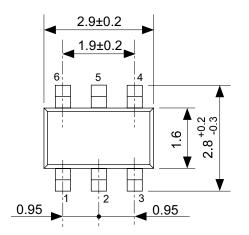
Item		Specification	
Size [mm]		114.3 x 76.2 x t1.6	
Material		FR-4	
Number of copper foil layer		2	
	1	Land pattern and wiring for testing: t0.070	
Copper foil layer [mm]	2	-	
Copper foil layer [min]	3	-	
	4	74.2 x 74.2 x t0.070	
Thermal via		-	

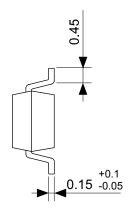
# (2) Board B

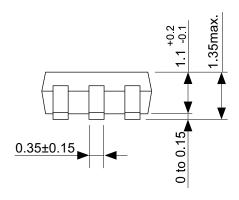


Item		Specification		
Size [mm]		114.3 x 76.2 x t1.6		
Material		FR-4		
Number of copper foil la	ayer	4		
	1	Land pattern and wiring for testing: t0.070		
Copper foil layer [mm]	2	74.2 x 74.2 x t0.035		
Copper foil layer [min]	3	74.2 x 74.2 x t0.035		
	4	74.2 x 74.2 x t0.070		
Thermal via		-		

No. SOT23x-A-Board-SD-2.0

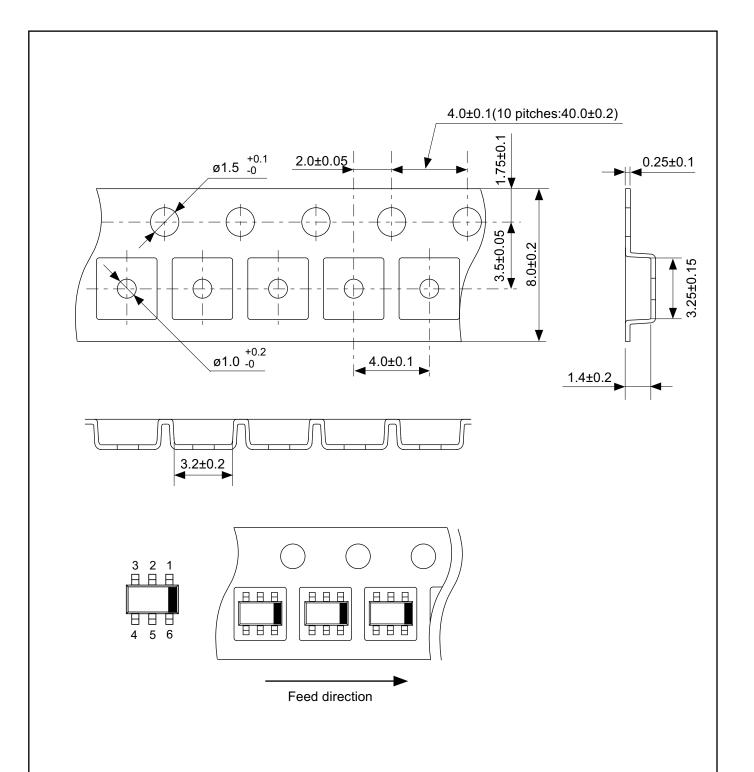






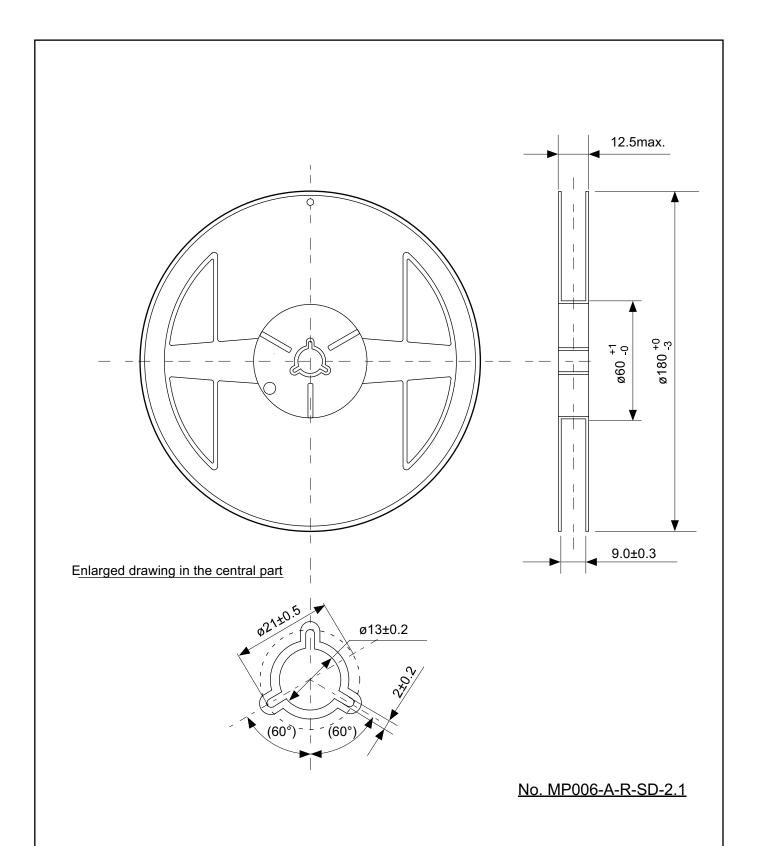
# No. MP006-A-P-SD-2.1

TITLE	SOT236-A-PKG Dimensions					
No.	MP006-A-P-SD-2.1					
ANGLE	<b>*</b>					
UNIT	mm					
ABLIC Inc.						



# No. MP006-A-C-SD-3.1

TITLE	SOT236-A-Carrier Tape					
No.	MP006-A-C-SD-3.1					
ANGLE						
UNIT	mm					
ABLIC Inc.						



TITLE	SOT236-A-Reel				
No.	MP006-A-R-SD-2.1				
ANGLE	QTY 3,000				
UNIT	mm				
ABLIC Inc.					

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